NSN 5962-01-288-6900

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View Online at https://aerobasegroup.com/nsn/5962-01-288-6900

Body Length: 0.840 inches **Body Width:** Between 0.220 inches and 0.310 inches **Body Height:** 0.185 inches **Maximum Power Dissipation Rating:** 739.0 milliwatts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius **Features Provided:** Schottky and bipolar and programmable and monolithic **Inclosure Material:** Ceramic Inclosure Configuration: Dual-in-line **Output Logic Form:** Transistor-transistor logic **Input Circuit Pattern:** 10 input **Case Outline Source And Designator:** D-2 mil-m-38510 **Terminal Surface Treatment:** Solder Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source **Time Rating Per Chacteristic:** 75.00 nanoseconds propagation delay time, low to high level output and 75.00 nanoseconds propagation delay time, high to low level output Memory Device Type: Rom **Test Data Document:**

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

16 printed circuit

Specification Data:

81349-mil-m-38510/203 government specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

A458a0

